(b) Amendment to the Claims

Please cancel claims 6, 8, 12-14, 20, 22 and 26-30 without prejudice or disclaimer of subject matter.

Kindly amend claims 1, 10, 11, 15, 24 and 25 as follows. A detailed listing of all the claims is provided.

- 1. (Currently Amended) An exhaust processing method of exhausting a processing space for subjecting a substrate or a film to plasma processing with plasma, which comprises:
- (a) providing <u>a</u> chemical-reaction inducing <u>unitmeans</u> having a heating element comprising a first metal member in an exhaust line, said exhaust line connecting the processing space and an exhaust <u>unitmeans</u> for exhausting the processing space, wherein the first metal member is connected to a power source;
- (b) providing <u>a</u> plasma blocking <u>unitmeans</u> consisting of a second metal member electrically grounded between the processing space and the first metal member; <u>wherein the chemical-reaction inducing unit is provided at a position where the plasma reaches and the plasma blocking unit blocks the plasma from reaching the chemical-reaction inducing unit; and</u>
- (c) causing chemical reaction of at least either an unreacted gas or a byproduct exhausted from the processing space via heat from said heating element while
 blocking plasma in the processing space from reaching the chemical-reaction inducing
 means via said plasma blocking means unit acts to reduce electron number density in the
 plasma reaching the chemical-reaction inducing unit by at least 90%.

2. - 9. (Cancelled)

- 10. (Currently Amended) The exhaust processing method according to claim 1, wherein one or more linear members or a linear member formed by a spiral winding are used as the <u>unit means</u> for blocking plasma.
- 11. (Currently Amended) The exhaust processing method according to claim 1, wherein a mesh is used as the <u>unitmeans</u> for blocking plasma.

12.-14. (Cancelled)

- 15. (Currently Amended) A plasma processing method for subjecting a substrate or a film to [[plasma]] processing with plasma, which comprises:
- (a) arranging a chemical-reaction inducing <u>unitmeans</u> having a heating element comprising a first metal member in an exhaust line, said exhaust line connecting a processing space for plasma processing and an exhaust <u>pumpmeans</u> for exhausting the processing space, wherein the first metal member is connected to a power source;
- (b) providing a plasma blocking <u>unitmeans</u> consisting of a second metal member electrically grounded between the processing space and the first metal member; wherein the chemical reaction inducing unit is provided at a position where the plasma reaches and the plasma blocking unit blocks the plasma from reaching the chemical reaction inducing unit; and

(c) causing chemical reaction of at least either an unreacted gas or a by-product exhausted from the processing space via heat from said heating element while blocking plasma in the processing space from reaching the chemical reaction inducing means via said plasma blocking means unit acts to reduce electron number density in the plasma reaching the chemical-reaction inducing unit by at least 90%.

16. - 23. (Cancelled)

- 24. (Currently Amended) The plasma processing method according to claim 15, wherein one or more linear members or a linear member formed by a spiral winding are used as the <u>unitmeans</u> for blocking plasma.
- 25. (Currently Amended) The plasma processing method according to claim 15, wherein a mesh is used as the <u>unitmeans</u> for blocking plasma.

26. - 50. (Cancelled)